



Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	53
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.85V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TQFP
Supplier Device Package	64-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg232f1024-qfp64t

1 Ordering Information

Table 1.1 (p. 2) shows the available EFM32GG232 devices.

Table 1.1. Ordering Information

Ordering Code	Flash (kB)	RAM (kB)	Max Speed (MHz)	Supply Voltage (V)	Temperature (°C)	Package
EFM32GG232F512G-E-QFP64	512	128	48	1.98 - 3.8	-40 - 85	TQFP64
EFM32GG232F1024G-E-QFP64	1024	128	48	1.98 - 3.8	-40 - 85	TQFP64

Adding the suffix 'R' to the part number (e.g. EFM32GG232F512G-E-QFP64R) denotes tape and reel.

Visit **www.silabs.com** for information on global distributors and representatives.

2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32GG microcontroller. The flash memory is readable and writable from both the Cortex-M3 and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

2.1.4 Direct Memory Access Controller (DMA)

The Direct Memory Access (DMA) controller performs memory operations independently of the CPU. This has the benefit of reducing the energy consumption and the workload of the CPU, and enables the system to stay in low energy modes when moving for instance data from the USART to RAM or from the External Bus Interface to a PWM-generating timer. The DMA controller uses the PL230 μ DMA controller licensed from ARM.

2.1.5 Reset Management Unit (RMU)

The RMU is responsible for handling the reset functionality of the EFM32GG.

2.1.6 Energy Management Unit (EMU)

The Energy Management Unit (EMU) manage all the low energy modes (EM) in EFM32GG microcontrollers. Each energy mode manages if the CPU and the various peripherals are available. The EMU can also be used to turn off the power to unused SRAM blocks.

2.1.7 Clock Management Unit (CMU)

The Clock Management Unit (CMU) is responsible for controlling the oscillators and clocks on-board the EFM32GG. The CMU provides the capability to turn on and off the clock on an individual basis to all peripheral modules in addition to enable/disable and configure the available oscillators. The high degree of flexibility enables software to minimize energy consumption in any specific application by not wasting power on peripherals and oscillators that are inactive.

2.1.8 Watchdog (WDOG)

The purpose of the watchdog timer is to generate a reset in case of a system failure, to increase application reliability. The failure may e.g. be caused by an external event, such as an ESD pulse, or by a software failure.

2.1.9 Peripheral Reflex System (PRS)

The Peripheral Reflex System (PRS) system is a network which lets the different peripheral module communicate directly with each other without involving the CPU. Peripheral modules which send out Reflex signals are called producers. The PRS routes these reflex signals to consumer peripherals which apply actions depending on the data received. The format for the Reflex signals is not given, but edge triggers and other functionality can be applied by the PRS.

2.1.10 Inter-Integrated Circuit Interface (I2C)

The I²C module provides an interface between the MCU and a serial I²C-bus. It is capable of acting as both a master and a slave, and supports multi-master buses. Both standard-mode, fast-mode and fast-mode plus speeds are supported, allowing transmission rates all the way from 10 kbit/s up to 1 Mbit/s. Slave arbitration and timeouts are also provided to allow implementation of an SMBus compliant system. The interface provided to software by the I²C module, allows both fine-grained control of the transmission

2.1.19 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.20 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.21 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 8 external pins and 6 internal signals.

2.1.22 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has two single ended output buffers which can be combined into one differential output. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.23 Operational Amplifier (OPAMP)

The EFM32GG232 features 3 Operational Amplifiers. The Operational Amplifier is a versatile general purpose amplifier with rail-to-rail differential input and rail-to-rail single ended output. The input can be set to pin, DAC or OPAMP, whereas the output can be pin, OPAMP or ADC. The current is programmable and the OPAMP has various internal configurations such as unity gain, programmable gain using internal resistors etc.

2.1.24 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface (LESENSE[™]), is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.25 Backup Power Domain

The backup power domain is a separate power domain containing a Backup Real Time Counter, BURTC, and a set of retention registers, available in all energy modes. This power domain can be configured to automatically change power source to a backup battery when the main power drains out. The backup power domain enables the EFM32GG232 to keep track of time and retain data, even if the main power source should drain out.

2.1.26 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data

Module	Configuration	Pin Connections
PCNT0	Full configuration, 16-bit count register	PCNT0_S[1:0]
PCNT1	Full configuration, 8-bit count register	PCNT1_S[1:0]
PCNT2	Full configuration, 8-bit count register	PCNT2_S[1:0]
ACMP0	Full configuration	ACMP0_CH[7:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:0], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0], DAC0_OUTxALT
OPAMP		
AES	Full configuration	NA
GPIO	53 pins	Available pins are shown in Table 4.3 (p. 55)

2.3 Memory Map

The EFM32GG232 memory map is shown in Figure 2.2 (p. 8), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32GG232 Memory Map with largest RAM and Flash sizes

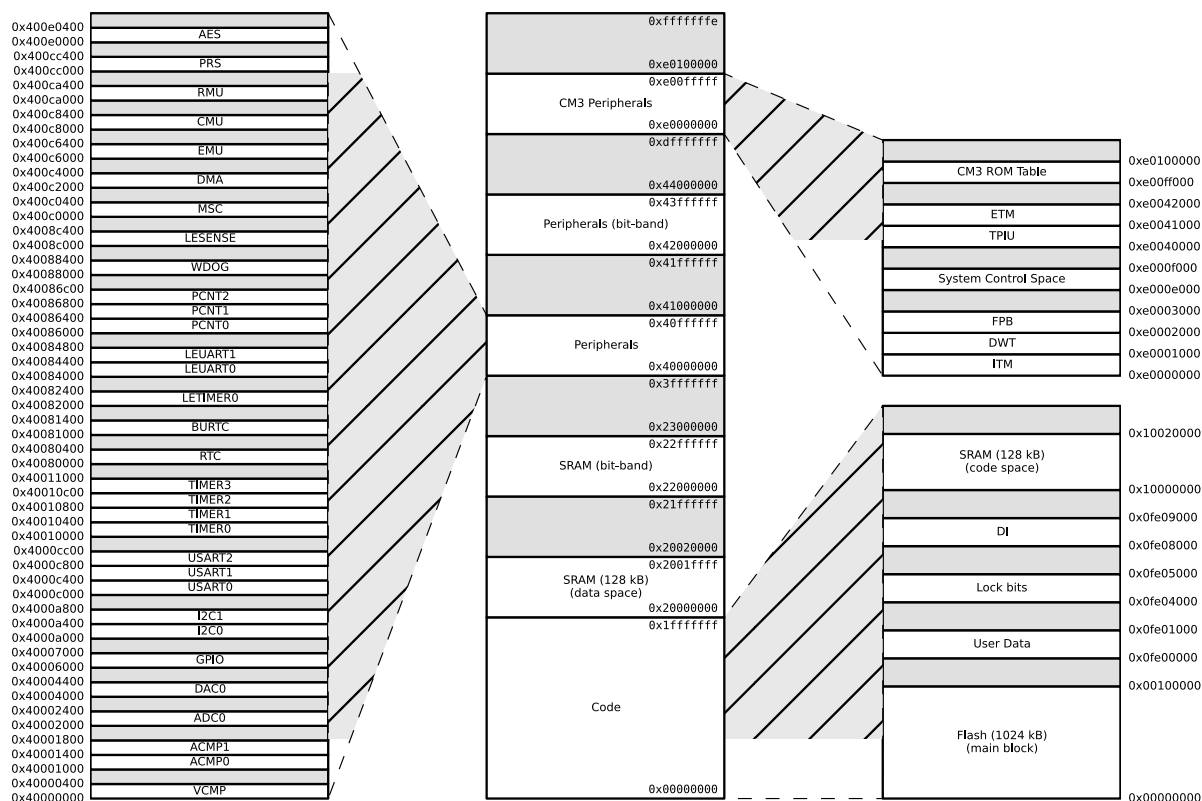


Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{BODextthr-}	BOD threshold on falling external supply voltage	EM0	1.74		1.96	V
		EM2	1.74		1.98	V
V _{BODintthr-}	BOD threshold on falling internally regulated supply voltage		1.57		1.70	V
V _{BODextthr+}	BOD threshold on rising external supply voltage			1.85	1.98	V
V _{PORthr+}	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t _{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
C _{DECOUPLE}	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC _{FLASH}	Flash erase cycles before failure		20000			cycles
RET _{FLASH}	Flash data retention	T _{AMB} <150°C	10000			h
		T _{AMB} <85°C	10			years
		T _{AMB} <70°C	20			years
t _{W_PROG}	Word (32-bit) programming time		20			μs
t _{PERASE}	Page erase time	LPERASE == 0	20	20.4	20.8	ms
		LPERASE == 1	40	40.4	40.8	ms
t _{DERASE}	Device erase time				161.6	ms
I _{ERASE}	Erase current	LPERASE == 0			14 ¹	mA
		LPERASE == 1			7 ¹	mA
I _{WRITE}	Write current	LPWRITE == 0			14 ¹	mA
		LPWRITE == 1			7 ¹	mA
V _{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

¹ Measured at 25°C

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		Sinking 20 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.20V_{DD}$	V
I_{IOLEAK}	Input leakage current	High Impedance IO connected to GROUND or V_{DD}		± 0.1	± 40	nA
R_{PU}	I/O pin pull-up resistor			40		kOhm
R_{PD}	I/O pin pull-down resistor			40		kOhm
R_{IOESD}	Internal ESD series resistor			200		Ohm
$t_{IOGLITCH}$	Pulse width of pulses to be removed by the glitch suppression filter		10		50	ns
t_{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capacitance $C_L=12.5-25$ pF.	$20+0.1C_L$		250	ns
		GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance $C_L=350-600$ pF	$20+0.1C_L$		250	ns
V_{IOHYST}	I/O pin hysteresis ($V_{IOTHR+} - V_{IOTHR-}$)	$V_{DD} = 1.98 - 3.8$ V	$0.10V_{DD}$			V

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{HFRCO}	Current consumption (Production test condition = 14MHz)	$f_{\text{HFRCO}} = 28 \text{ MHz}$		165	190	μA
		$f_{\text{HFRCO}} = 21 \text{ MHz}$		134	155	μA
		$f_{\text{HFRCO}} = 14 \text{ MHz}$		106	120	μA
		$f_{\text{HFRCO}} = 11 \text{ MHz}$		94	110	μA
		$f_{\text{HFRCO}} = 6.6 \text{ MHz}$		77	90	μA
		$f_{\text{HFRCO}} = 1.2 \text{ MHz}$		25	32	μA
$\text{TUNESTEP}_{\text{HFRCO}}$	Frequency step for LSB change in TUNING value			0.3 ³		%

¹For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

²For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

³The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.11. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature

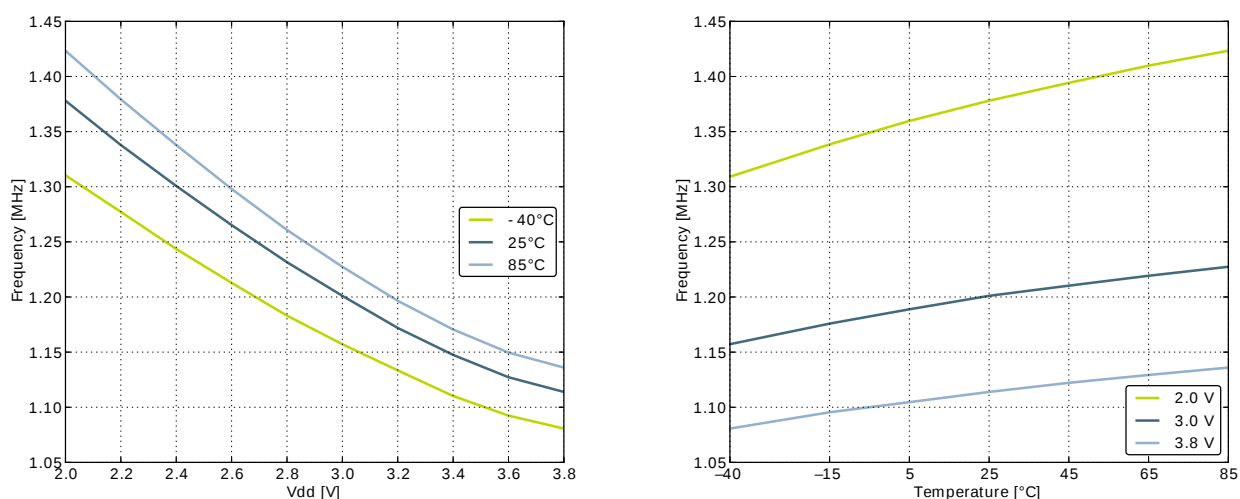


Figure 3.12. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature

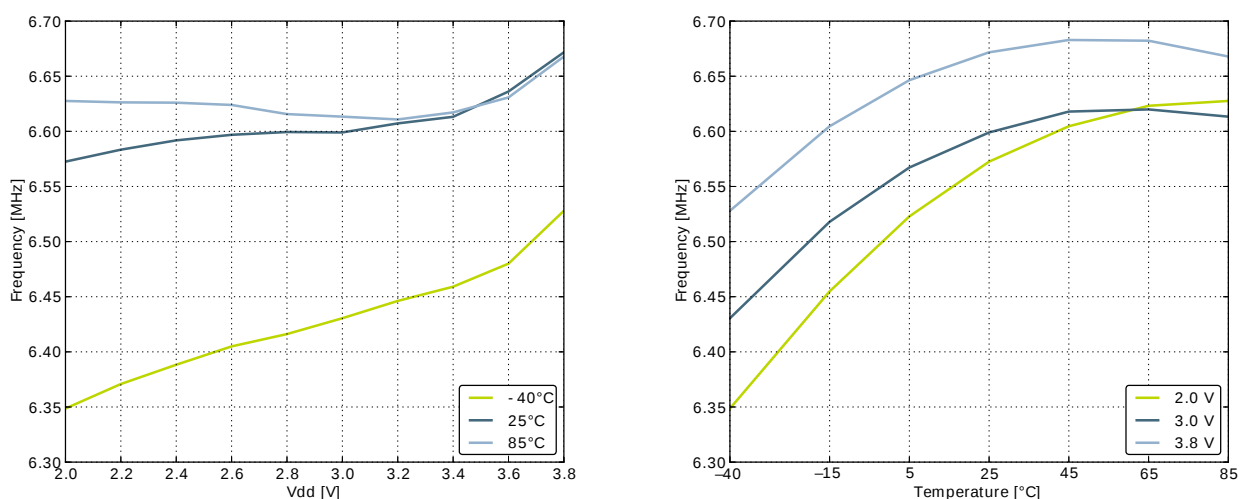
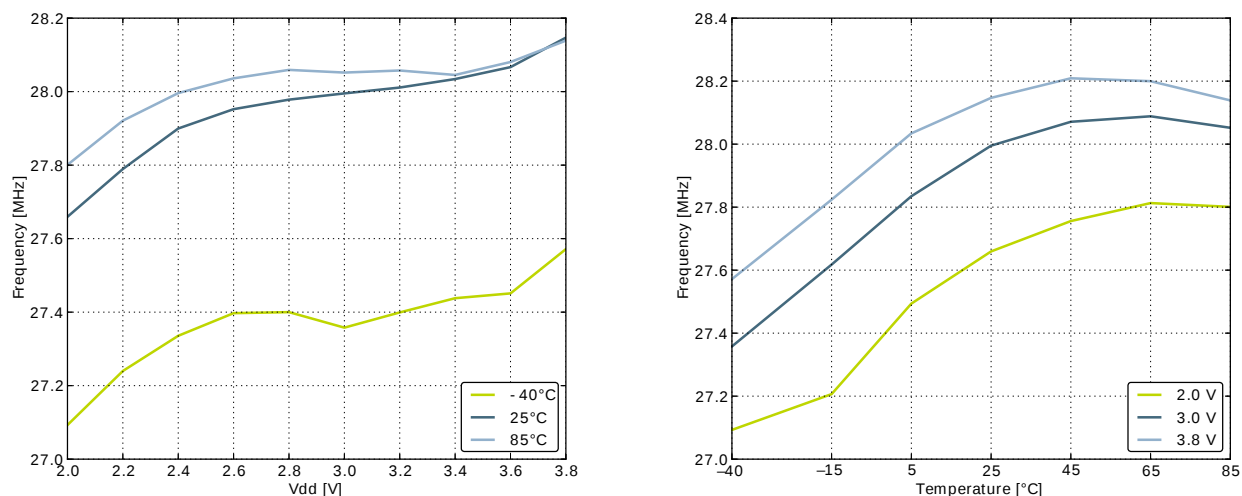


Figure 3.16. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature

3.9.5 AUXHFRCO

Table 3.12. AUXHFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{AUXHFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48 ¹	6.60 ¹	6.72 ¹	MHz
		1 MHz frequency band	1.15 ²	1.20 ²	1.25 ²	MHz
$t_{\text{AUXHFRCO_settling}}$	Settling time after start-up	$f_{\text{AUXHFRCO}} = 14 \text{ MHz}$		0.6		Cycles
$\text{DC}_{\text{AUXHFRCO}}$	Duty cycle	$f_{\text{AUXHFRCO}} = 14 \text{ MHz}$	48.5	50	51	%
$\text{TUNESTEP}_{\text{AUXHFRCO}}$	Frequency step for LSB change in TUNING value			0.3 ³		%

¹For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

²For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

³The TUNING field in the CMU_AUXHFRCOCTRL register may be used to adjust the AUXHFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the AUXHFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Symbol	Parameter	Condition	Min	Typ	Max	Unit
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MOhm
R _{ADCFILT}	Input RC filter resistance			10		kOhm
C _{ADCFILT}	Input RC filter/de-coupling capacitance			250		fF
f _{ADCCLK}	ADC Clock Frequency				13	MHz
t _{ADCCONV}	Conversion time	6 bit	7			ADC-CLK Cycles
		8 bit	11			ADC-CLK Cycles
		12 bit	13			ADC-CLK Cycles
t _{ADCACQ}	Acquisition time	Programmable	1		256	ADC-CLK Cycles
t _{ADCACQVDD3}	Required acquisition time for VDD/3 reference		2			μs
t _{ADCSTART}	Startup time of reference generator and ADC core in NORMAL mode			5		μs
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		μs
SNR _{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V _{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, 2xV _{DD} reference		69		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		200 kSamples/s, 12 bit, differential, $2 \times V_{DD}$ reference		69		dB
SFDR _{ADC}	Spurious-Free Dynamic Range (SFDR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		64		dBc
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		76		dBc
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		73		dBc
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		66		dBc
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		77		dBc
		1 MSamples/s, 12 bit, differential, V_{DD} reference		76		dBc
		1 MSamples/s, 12 bit, differential, $2 \times V_{DD}$ reference		75		dBc
		1 MSamples/s, 12 bit, differential, 5V reference		69		dBc
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		76		dBc
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		79		dBc
		200 kSamples/s, 12 bit, differential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V_{DD} reference	68	79		dBc
		200 kSamples/s, 12 bit, differential, $2 \times V_{DD}$ reference		79		dBc
V _{ADCOFFSET}	Offset voltage	After calibration, single ended		0.3		mV
		After calibration, differential	-3	0.3	3	mV
TGRAD _{ADCTH}	Thermometer output gradient			-1.92		mV/°C
				-6.3		ADC Codes/°C
DNL _{ADC}	Differential non-linearity (DNL)	$V_{DD} = 3.0$ V, external 2.5V reference	-1	±0.7	4	LSB
INL _{ADC}	Integral non-linearity (INL), End point method			±1.2	±3.0	LSB
MC _{ADC}	No missing codes		11.999 ¹	12		bits

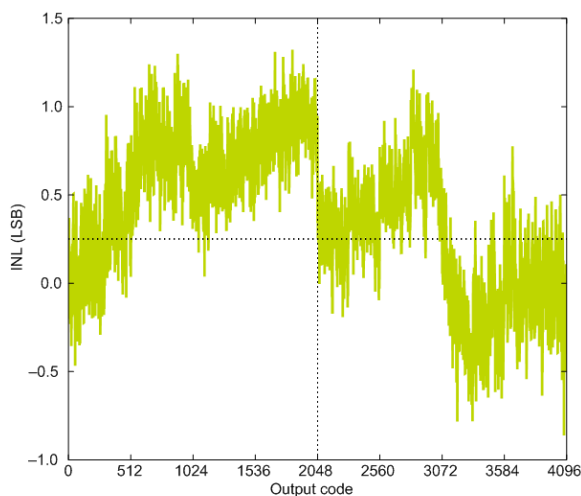
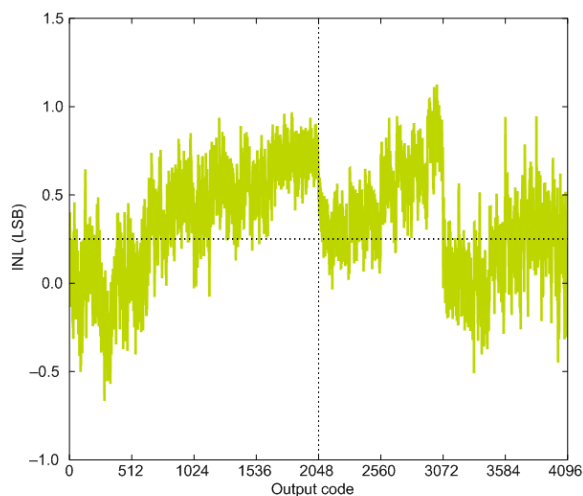
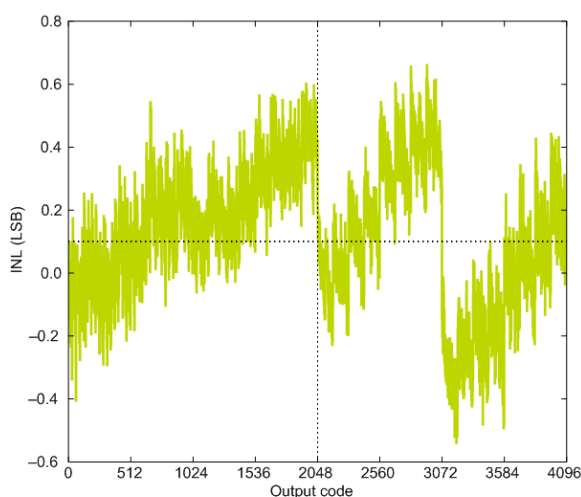
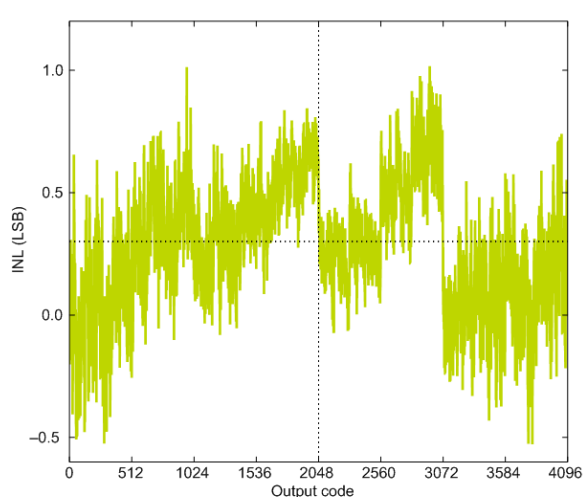
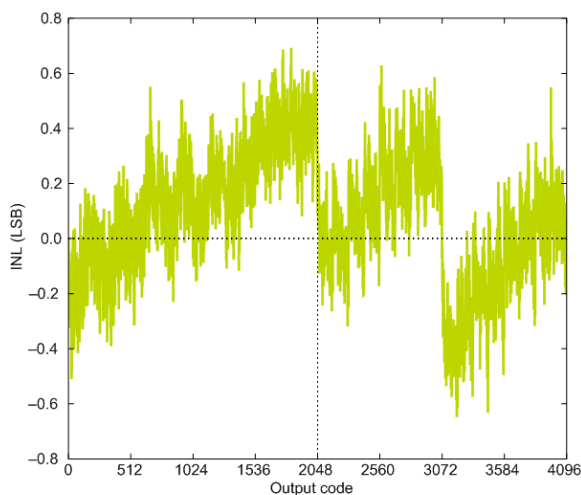
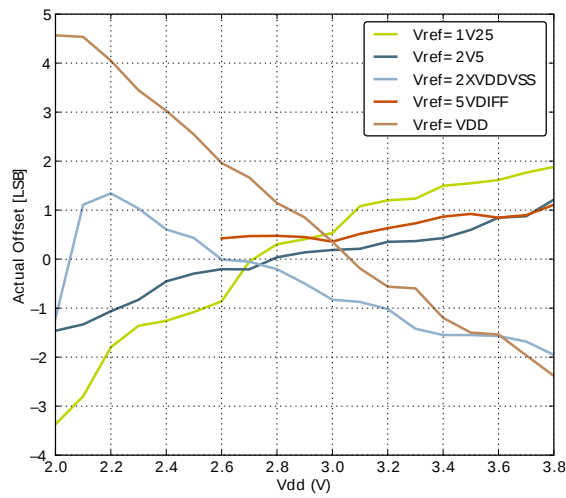
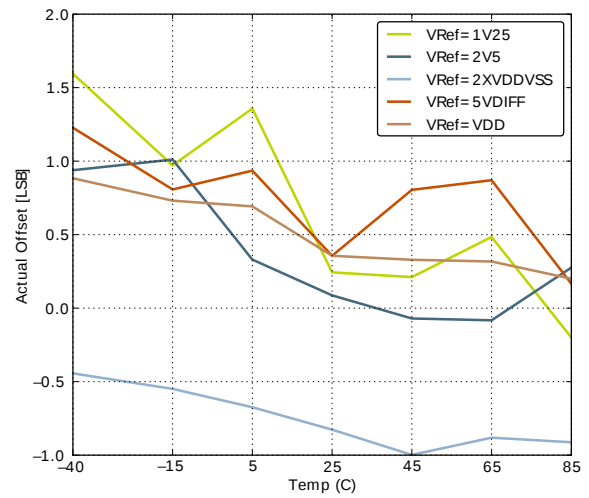
Figure 3.20. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C**1.25V Reference****2.5V Reference****2XVDDVSS Reference****5VDIFF Reference****VDD Reference**

Figure 3.22. ADC Absolute Offset, Common Mode = $V_{dd}/2$

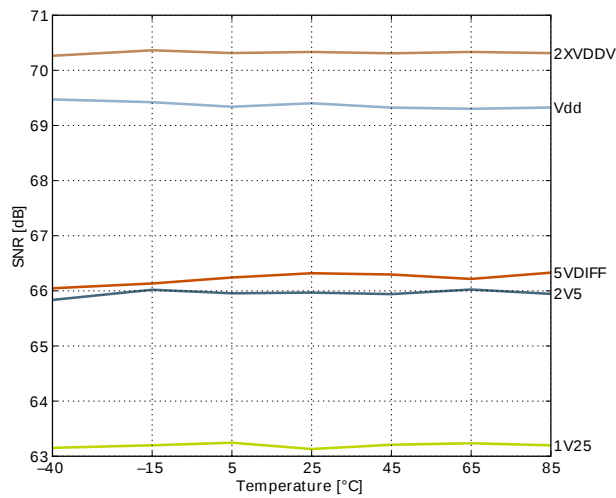


Offset vs Supply Voltage, Temp = 25°C

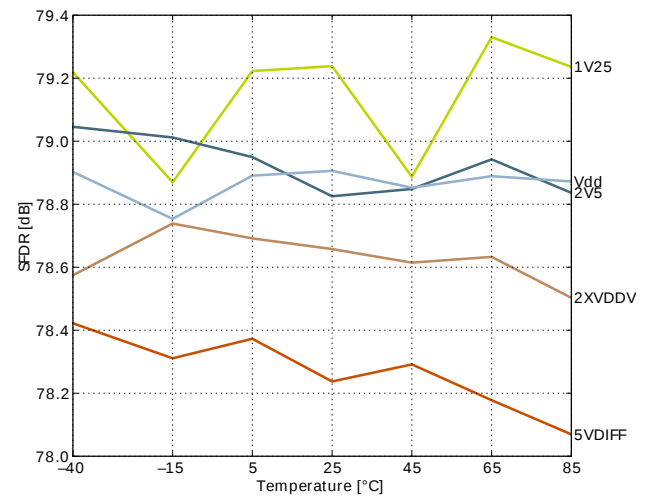


Offset vs Temperature, $V_{dd} = 3V$

Figure 3.23. ADC Dynamic Performance vs Temperature for all ADC References, $V_{dd} = 3V$



Signal to Noise Ratio (SNR)

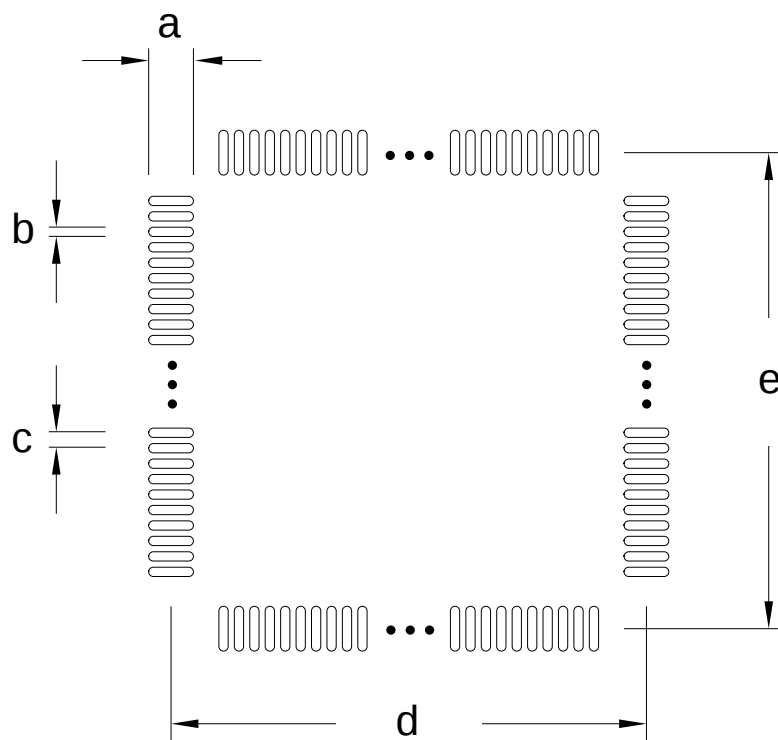


Spurious-Free Dynamic Range (SFDR)

3.17 Digital Peripherals

Table 3.24. Digital Peripherals

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{USART}	USART current	USART idle current, clock enabled		4.9		μA/ MHz
I _{UART}	UART current	UART idle current, clock enabled		3.4		μA/ MHz
I _{LEUART}	LEUART current	LEUART idle current, clock enabled		140		nA
I _{I2C}	I2C current	I2C idle current, clock enabled		6.1		μA/ MHz
I _{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		6.9		μA/ MHz
I _{LETIMER}	LETIMER current	LETIMER idle current, clock enabled		119		nA
I _{PCNT}	PCNT current	PCNT idle current, clock enabled		54		nA
I _{RTC}	RTC current	RTC idle current, clock enabled		54		nA
I _{AES}	AES current	AES idle current, clock enabled		3.2		μA/ MHz
I _{GPIO}	GPIO current	GPIO idle current, clock enabled		3.7		μA/ MHz
I _{PRS}	PRS current	PRS idle current		3.5		μA/ MHz
I _{DMA}	DMA current	Clock enable		11.0		μA/ MHz

Figure 5.3. TQFP64 PCB Stencil Design**Table 5.3. QFP64 PCB Stencil Design Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)
a	1.50
b	0.20
c	0.50
d	11.50
e	11.50

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 56) .

5.2 Soldering Information

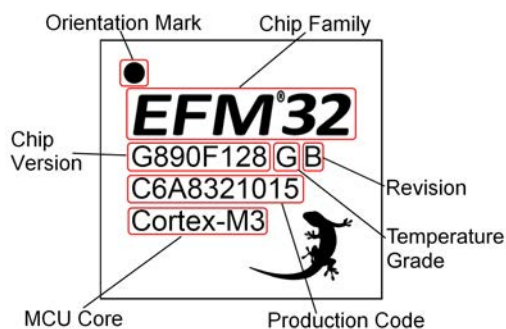
The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 61) .

6.3 Errata

Please see the errata document for EFM32GG232 for description and resolution of device erratas. This document is available in Simplicity Studio and online at:
<http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit>

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Other minor corrections.

7.7 Revision 0.98

May 25th, 2012

Corrected EM3 current consumption in the Electrical Characteristics section.

7.8 Revision 0.96

February 28th, 2012

Added reference to errata document.

Corrected TQFP64 package drawing.

Updated PCB land pattern, solder mask and stencil design.

7.9 Revision 0.95

September 28th, 2011

Flash configuration for Giant Gecko is now 1024KB or 512KB. For flash sizes below 512KB, see the Leopard Gecko Family.

Corrected operating voltage from 1.8 V to 1.85 V.

Added rising POR level to Electrical Characteristics section.

Updated Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup.

Added Gain error drift and Offset error drift to ADC table.

Added Opamp pinout overview.

Added reference to errata document.

Corrected TQFP64 package drawing.

Updated PCB land pattern, solder mask and stencil design.

7.10 Revision 0.90

June 29th, 2011

Initial preliminary release.

B Contact Information

Silicon Laboratories Inc.

400 West Cesar Chavez

Austin, TX 78701

Please visit the Silicon Labs Technical Support web page:

<http://www.silabs.com/support/pages/contacttechnicalsupport.aspx>

and register to submit a technical support request.

Table of Contents

1. Ordering Information	2
2. System Summary	3
2.1. System Introduction	3
2.2. Configuration Summary	7
2.3. Memory Map	8
3. Electrical Characteristics	9
3.1. Test Conditions	9
3.2. Absolute Maximum Ratings	9
3.3. General Operating Conditions	9
3.4. Current Consumption	10
3.5. Transition between Energy Modes	12
3.6. Power Management	12
3.7. Flash	13
3.8. General Purpose Input Output	14
3.9. Oscillators	22
3.10. Analog Digital Converter (ADC)	27
3.11. Digital Analog Converter (DAC)	37
3.12. Operational Amplifier (OPAMP)	38
3.13. Analog Comparator (ACMP)	42
3.14. Voltage Comparator (VCMP)	44
3.15. I2C	44
3.16. USART SPI	45
3.17. Digital Peripherals	47
4. Pinout and Package	48
4.1. Pinout	48
4.2. Alternate Functionality Pinout	51
4.3. GPIO Pinout Overview	55
4.4. Opamp Pinout Overview	55
4.5. TQFP64 Package	56
5. PCB Layout and Soldering	58
5.1. Recommended PCB Layout	58
5.2. Soldering Information	60
6. Chip Marking, Revision and Errata	61
6.1. Chip Marking	61
6.2. Revision	61
6.3. Errata	61
7. Revision History	62
7.1. Revision 1.40	62
7.2. Revision 1.30	62
7.3. Revision 1.21	63
7.4. Revision 1.20	63
7.5. Revision 1.10	63
7.6. Revision 1.00	64
7.7. Revision 0.98	64
7.8. Revision 0.96	64
7.9. Revision 0.95	64
7.10. Revision 0.90	64
A. Disclaimer and Trademarks	65
A.1. Disclaimer	65
A.2. Trademark Information	65
B. Contact Information	66
B.1.	66

List of Figures

2.1. Block Diagram	3
2.2. EFM32GG232 Memory Map with largest RAM and Flash sizes	8
3.1. EM2 current consumption. RTC prescaled to 1 Hz, 32.768 kHz LFRCO.	11
3.2. EM3 current consumption.	11
3.3. EM4 current consumption.	12
3.4. Typical Low-Level Output Current, 2V Supply Voltage	16
3.5. Typical High-Level Output Current, 2V Supply Voltage	17
3.6. Typical Low-Level Output Current, 3V Supply Voltage	18
3.7. Typical High-Level Output Current, 3V Supply Voltage	19
3.8. Typical Low-Level Output Current, 3.8V Supply Voltage	20
3.9. Typical High-Level Output Current, 3.8V Supply Voltage	21
3.10. Calibrated LFRCO Frequency vs Temperature and Supply Voltage	23
3.11. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature	24
3.12. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature	24
3.13. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature	25
3.14. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature	25
3.15. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature	25
3.16. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature	26
3.17. Integral Non-Linearity (INL)	31
3.18. Differential Non-Linearity (DNL)	32
3.19. ADC Frequency Spectrum, V _{dd} = 3V, Temp = 25°C	33
3.20. ADC Integral Linearity Error vs Code, V _{dd} = 3V, Temp = 25°C	34
3.21. ADC Differential Linearity Error vs Code, V _{dd} = 3V, Temp = 25°C	35
3.22. ADC Absolute Offset, Common Mode = V _{dd} / 2	36
3.23. ADC Dynamic Performance vs Temperature for all ADC References, V _{dd} = 3V	36
3.24. ADC Temperature sensor readout	37
3.25. OPAMP Common Mode Rejection Ratio	40
3.26. OPAMP Positive Power Supply Rejection Ratio	40
3.27. OPAMP Negative Power Supply Rejection Ratio	41
3.28. OPAMP Voltage Noise Spectral Density (Unity Gain) V _{out} =1V	41
3.29. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)	41
3.30. ACMP Characteristics, V _{dd} = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1	43
3.31. SPI Master Timing	45
3.32. SPI Slave Timing	46
4.1. EFM32GG232 Pinout (top view, not to scale)	48
4.2. Opamp Pinout	55
4.3. TQFP64	56
5.1. TQFP64 PCB Land Pattern	58
5.2. TQFP64 PCB Solder Mask	59
5.3. TQFP64 PCB Stencil Design	60
6.1. Example Chip Marking (top view)	61

List of Equations

3.1. Total ACMP Active Current 42

3.2. VCMP Trigger Level as a Function of Level Setting 44